

$^{22}\text{Si}$   $\varepsilon$  decay    1996Bl11

Type	Author	History	Citation	Literature Cutoff Date
Full Evaluation	M. Shamsuzzoha Basunia		NDS 127, 69(2015)	1-Apr-2015

Parent:  $^{22}\text{Si}$ : E=0.0;  $J^\pi=0^+$ ;  $T_{1/2}=29$  ms 2;  $Q(\varepsilon)=15137$  SY; % $\varepsilon$ +% $\beta^+$  decay=100.0Produced by  $^{58}\text{Ni}({}^{36}\text{Ar},\text{x})$  E( ${}^{36}\text{Ar}$ )=95 MeV/A. Measured half-life,  $\beta^+$ -delayed proton emission. $^{22}\text{Al}$  Levels

E(level) <sup>†</sup>	$J^\pi$ <sup>†</sup>
0.0	(4) <sup>+</sup>
1850	1 <sup>+</sup>
2210	1 <sup>+</sup>

<sup>†</sup> From Adopted Levels. $\varepsilon, \beta^+$  radiations

E(decay)	E(level)	I $\beta^+$ <sup>†</sup>	Log ft	I( $\varepsilon+\beta^+$ ) <sup>†</sup>	Comments
(12927 SY)	2210	$\geq 6$	<4.8	$\geq 6$	av E $\beta$ =5152.19
(13287 SY)	1850	$\geq 22$	<4.3	$\geq 22$	av E $\beta$ =5331.21

<sup>†</sup> Absolute intensity per 100 decays.